

Please amend claim 1 and add new claims 2-26 as follows.

1. (Currently amended) An active matrix display device comprising:

~~a substrate having an insulating surface;~~

a signal line formed over a substrate;

a first thin film transistor having a first channel region and a first pair of impurity regions formed in a first semiconductor film over said substrate wherein a first gate electrode of said first thin film transistor is electrically connected to said signal line;

a voltage supply line formed over said substrate;

a second thin film transistor having a second channel region and a second pair of impurity regions formed in a second semiconductor film over said substrate wherein one of said second pair of impurity regions is electrically connected to said voltage supply line; and

a pixel electrode formed over said substrate wherein said pixel electrode is electrically connected to said voltage supply line through at least said second thin film transistor another one of said second pair of impurity regions,

wherein at least one of said first and second thin film transistors has at least one LDD region between the channel region and at least one of the impurity regions.

2. (New) An active matrix display device according to claim 1, wherein at least one of said first and second gate electrodes comprises a material selected from the group consisting of Ti, Al, Ta and Cr.

3. (New) An active matrix display device according to claim 1, wherein said LDD region contains an impurity element having one conductivity at a concentration lower than the impurity region.

4. (New) An active matrix display device according to claim 1, wherein said first and second semiconductor films comprise germanium.

5. (New) An active matrix display device according to claim 1, wherein said first and second semiconductor films comprise crystalline silicon.

6. (New) An active matrix display device comprising:

a signal line formed over a substrate;

a first thin film transistor having a first channel region and first source and drain regions formed in a first semiconductor film over said substrate wherein a first gate electrode of said first thin film transistor is electrically connected to said signal line;

a voltage supply line formed over said substrate;

a second thin film transistor having a second channel region and second source and drain regions formed in a second semiconductor film over said substrate wherein said second source region is electrically connected to said voltage supply line; and

a pixel electrode formed over said substrate wherein said pixel electrode is electrically connected to said second drain region,

wherein at least one of the first and second transistors has at least one LDD region between the channel region and at least one of the source and drain regions.

7. (New) An active matrix display device according to claim 6, wherein at least one of said first and second gate electrodes comprises a material selected from the group consisting of Ti, Al, Ta and Cr.

8. (New) An active matrix display device according to claim 6, wherein said LDD region contains an impurity element having one conductivity at a concentration lower than the source and drain regions.

9. (New) An active matrix display device according to claim 6, wherein said first and second semiconductor films comprise germanium.

10. (New) An active matrix display device according to claim 6, wherein said first and second semiconductor films comprise crystalline silicon.

11. (New) An active matrix display device comprising:

a signal line formed over a substrate;

a first thin film transistor having a first channel region and a first pair of impurity regions formed in a first semiconductor film over said substrate wherein a first gate electrode of said first thin film transistor is electrically connected to said signal line;

a voltage supply line formed over said substrate;

a second thin film transistor having a second channel region and a second pair of impurity regions formed in a second semiconductor film over said substrate wherein one of said second pair of impurity regions is electrically connected to said voltage supply line; and

a pixel electrode formed over said substrate wherein said pixel electrode is electrically connected to another one of said second pair of impurity regions,

wherein at least one of said first and second thin film transistors has at least one LDD region between the channel region and at least one of the impurity regions,

wherein the conductivity of said first thin film transistor is different from the conductivity of said second thin film transistor.

12. (New) An active matrix display device according to claim 11, wherein at least one of said first and second gate electrodes comprises a material selected from the group consisting of Ti, Al, Ta and Cr.

13. (New) An active matrix display device according to claim 11, wherein said LDD region contains an impurity element having one conductivity at a concentration lower than the impurity region.

14. (New) An active matrix display device according to claim 11, wherein said first and second semiconductor films comprise germanium.

15. (New) An active matrix display device according to claim 11, wherein said first and second semiconductor films comprise crystalline silicon.

16. (New) An active matrix device comprising:

a signal line formed over a substrate;

a first thin film transistor having a first channel region and first source and drain regions formed in a first semiconductor film over said substrate wherein a first gate electrode of said first thin film transistor is electrically connected to said signal line;

a voltage supply line formed over said substrate;

a second thin film transistor having a second channel region and second source and drain regions formed in a second semiconductor film over said substrate wherein said second source region is electrically connected to said voltage supply line; and

a pixel electrode formed over said substrate wherein said pixel electrode is electrically connected to said second drain region,

wherein at least one of the first and second transistors has at least one LDD region between the channel region and at least one of the source and drain regions,

wherein the conductivity of said first thin film transistor is different from the conductivity of said second thin film transistor.

17. (New) An active matrix display device according to claim 16, wherein at least one of said first and second gate electrodes comprises a material selected from the group consisting of Ti, Al, Ta and Cr.

18. (New) An active matrix display device according to claim 16, wherein said LDD region contains an impurity element having one conductivity at a concentration lower than the source and drain regions.

19. (New) An active matrix display device according to claim 16, wherein said first and second semiconductor films comprise germanium.

20. (New) An active matrix display device according to claim 16, wherein said first and second semiconductor films comprise crystalline silicon.

21. (New) An active matrix display device comprising:

a signal line formed over a substrate;

a first thin film transistor having a first channel region interposed between a first pair of impurity regions, and a second pair of impurity regions between said first channel region and said first pair of impurity regions formed in a first semiconductor film over said substrate wherein a first gate electrode of said first thin film transistor is electrically connected to said signal line;

a voltage supply line formed over said substrate;

a second thin film transistor having a second channel region interposed between a third pair of impurity regions, and a fourth pair of impurity regions between said second channel region and said third pair of impurity regions formed in a second semiconductor film over said substrate wherein one of said second pair of impurity regions is electrically connected to said voltage supply line; and

a pixel electrode formed over said substrate wherein said pixel electrode is electrically connected to another one of said second pair of impurity regions.

22. (New) An active matrix display device according to claim 21, wherein at least one of said first and second gate electrodes comprises a material selected from the group consisting of Ti, Al, Ta and Cr.

23. (New) An active matrix display device according to claim 21, wherein said second pair of impurity regions contains an impurity element having one conductivity at a concentration lower than said first pair of impurity regions.

24. (New) An active matrix display device according to claim 21, wherein said fourth pair of impurity regions contains an impurity element having one conductivity at a concentration lower than said third pair of impurity regions.

25. (New) An active matrix display device according to claim 21, wherein said first and second semiconductor films comprise germanium.

26. (New) An active matrix display device according to claim 21, wherein said first and second semiconductor films comprise crystalline silicon.